

Power Management Switch IC Series or PCs and Digital Consumer Product





1ch Large Current Output USB High Side Switch ICs

BD2041AFJ,BD2051AFJ,BD6518FJ,BD6519FJ

No.09029EAT03

Description

Single channel high side switch IC for USB port is a high side switch having over current protection used in power supply line of universal serial bus (USB).

N-channel power MOSFET of low on resistance and low supply current are realized in this IC.

And, over current detection circuit, thermal shutdown circuit, under voltage lockout and soft start circuit are built in.

Features

1) Built-in low on resistance Nch MOS FET Switch.

Typ = $80m\Omega$ (BD2041AF/BD2051AFJ)

Typ = $100m\Omega$ (BD6518F/BD6519FJ)

- 2) Continuous current load 0.5A
- 3) Control input logic

Active-Low: BD2041AFJ/ BD6519FJ Active-High: BD2051AFJ/ BD6518FJ

- 4) Soft start circuit
- 5) Over current detection
- 6) Thermal shutdown
- 7) Under voltage lockout
- 8) Open drain error flag output
- 9) Reverse-current protection when power switch off
- 10) Power supply voltage range

2.7V~5.5V (BD2041AF/BD2051AFJ)

3.0V~5.5V (BD6518F/BD6519FJ)

11) Operating temperature range -40°C~85°C

Applications

USB hub in consumer appliances, Car accessory, PC, PC peripheral equipment, and so forth

●Lineup

Parameter	BD2041AFJ	BD2051AFJ	BD6518FJ	BD6519FJ
Continuous current load (A)	0.5	0.5	0.5	0.5
Output current at short (A)	1.0	1.0	1.1	1.1
Control input logic	Low	High	High	Low

Absolute Maximum Ratings

Parameter	Symbol	Limits	Unit
Supply voltage	Vin	-0.3 to 6.0	V
Enable voltage	VEN, V/EN	-0.3 to 6.0	V
/OC voltage	V/oc	-0.3 to 6.0	V
/OC current	IS/oc	10	mA
OUT voltage	Vout	-0.3 to 6.0	V
Storage temperature	Tstg	-55 to 150	°C
Power dissipation	PD	560 ^{*1}	mW

^{*1} In the case of exceeding Ta = 25°C, 4.48mW should be reduced per 1°C.

^{*} This chip is not designed to protect itself against radioactive rays.

X IN, EN (/EN), and /OC terminal of BD2041AFJ/BD2051AFJ correspond to VDD, CTRL, and FLAG terminal of BD6518FJ/BD6519FJ, respectively.

●Operating conditions ⊚BD2041AF/BD2051AFJ

Parameter	Symbol	Limits	Unit
Operating voltage	Vin	2.7 to 5.5	V
Operating temperature	Topr	-40 to 85	°C
Continuous output current	ILO	0 to 500	mA

©BD6518FJ/BD6519FJ

Parameter	Symbol	Limits	Unit
Operating voltage	Vin	3.0 to 5.5	V
Operating temperature	Topr	-40 to 85	Ô
Continuous output current	ILO	0 to 500	mA

•Electrical characteristics

©BD2041AFJ (Unless otherwise specified, VIN = 5.0V, Ta = 25°C)

Parameter	Cumbal		Limits		Unit	Condition
Parameter	Symbol	Min.	Typ.	Max.	UTIIL	Condition
Operating Current	IDD	-	90	120	μΑ	V/EN = 0V, OUT = OPEN
Standby Current	ISTB	-	0.01	1	μΑ	V/EN = 5V, OUT = OPEN
	V/EN	2.0	-	-	V	High input
/EN input voltage	V/EN	-	-	8.0	V	Low input
	V/EIN	-	-	0.4	V	Low input 2.7V≤ VIN ≤4.5V
/EN input current	l/EN	-1.0	0.01	1.0	μΑ	V/EN = 0V or V/EN = 5V
/OC output LOW voltage	V/oc	-	-	0.5	V	I/oc = 5mA
/OC output leak current	IL/oc	-	0.01	1	μΑ	V/oc = 5V
ON resistance	Ron	-	80	100	mΩ	IOUT = 500mA
Output current at short	Isc	0.7	1.0	1.3	А	Vin = 5V, Vout = 0V, CL = 100μF (RMS)
Output rise time	Ton1	-	1.2	10	ms	
Output turn on time	Ton2	-	1.5	20	ms	D 100 C ODEN
Output fall time	Toff1	-	1	20	μs	RL = 10Ω , CL = OPEN
Output turn off time	Toff2	-	3	40	μs	
UVLO threshold	VTUVH	2.1	2.3	2.5	V	Increasing VIN
OVEO tillesilold	VTUVL	2.0	2.2	2.4	V	Decreasing VIN

⊚BD6519FJ (Unless otherwise specified, VDD = 5.0V, Ta = 25°C)

Parameter	Symbol	Limits		Unit	Condition	
Farameter		Min.	Typ.	Max.	Offic	Condition
Operating Current	Inn	-	90	140	μA	VCTRL= 0V, OUT = OPEN
Standby Current	טטו	-	0.01	2	μA	VCTRL= 5V, OUT = OPEN
CTPL input voltage	VCTRL	2.5	-	-	V	High input
CTRL input voltage	VCIRL	-	-	0.7	V	Low input
CTRL input voltage	ICTRL	-1.0	0.01	1.0	μA	VCTRL = 0V or VCTRL = 5V
FLAG output resistance	RFLAG	-	180	450	Ω	IFLAG = 1mA
FLAG output leak current	ILFLAG	-	0.01	1	μA	VFLAG = 5V
FLAG output delay	TDFLAG	-	2.5	8	ms	
ON resistance	Ron	-	100	140	mΩ	VDD = 5V, IOUT = 500mA
ON resistance	KON	-	140	180	mΩ	VDD = 3.3V, IOUT = 500mA
Short circuit output current	Isc	0.6	-	1.6	Α	VDD = 5V , VOUT = 0V
Output leak current	ILEAK	-	-	10	μA	VCTRL = 5V
Output rise time	Ton1	-	1	4	ms	
Output turn on delay time	Ton2	-	1.3	6	ms	RL = 10Ω , CL = OPEN
Output fall time	Toff1	-	1	20	μs	RL - 1002, GL - OPEN
Output turn off delay time	Toff2	-	3	20	μs	
Thermal shutdown threshold	Trs	-	135	-	°C	Tj increase
LIVI O throubold	VTUVH	2.3	2.5	2.7	V	VDD increasing
UVLO threshold	VTUVL	2.1	2.3	2.5	V	VDD decreasing

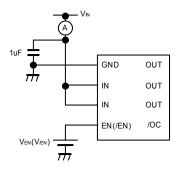
 \bigcirc BD2051AFJ (Unless otherwise specified, V_{IN} = 5.0V, Ta = 25°C)

Parameter	Symbol	Symbol Limits		Unit	Condition	
Farameter	Syllibol	Min.	Тур.	Max.	Unit	Condition
Operating Current	I _{DD}	-	90	120	μA	VEN = 5V, OUT = OPEN
Standby Current	I _{STB}	-	0.01	1	μA	VEN = 0V, OUT = OPEN
	V _{EN}	2.0	-	-	V	High input
EN input voltage		-	-	8.0	V	Low input
	V_{EN}	-	-	0.4	V	Low input 2.7V≤ VIN ≤4.5V
EN input current	I _{EN}	-1.0	0.01	1.0	μA	VEN = 0V or VEN = 5V
/OC output LOW voltage	V _{/OC}	-	-	0.5	V	I/oc = 5mA
/OC output leak current	IL _{/OC}	-	0.01	1	μA	V/oc = 5V
ON resistance	Ron	-	80	100	mΩ	IOUT = 500mA
Output current at short	Isc	0.7	1.0	1.3	Α	Vin = 5V, Vout = 0V, CL = 100μF (RMS)
Output rise time	T _{ON1}	-	1.2	10	ms	
Output turn on time	T _{ON2}	-	1.5	20	ms	D: = 100 C: = ODEN
Output fall time	T _{OFF1}	-	1	20	μs	$RL = 10\Omega$, $CL = OPEN$
Output turn off time	T _{OFF2}	-	3	40	μs	
LIVI O throshold	V_{TUVH}	2.1	2.3	2.5	V	Increasing VIN
UVLO threshold	V_{TUVL}	2.0	2.2	2.4	V	Decreasing VIN

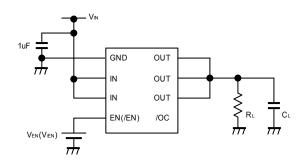
©BD6518FJ (Unless otherwise specified, VDD = 5.0V, Ta = 25°C)

©BD001010 (Offices otherwi	•	Limits		l lmit	0 - 111 -	
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Operating Current	laa	-	90	140	μΑ	VCTRL= 5V, OUT = OPEN
Standby Current	IDD	-	0.01	2	μA	VCTRL= 0V, OUT = OPEN
CTRL input voltage	VCTRL	2.5	-	-	V	High input
CTRL input voltage	VCIRL	-	-	0.7	V	Low input
CTRL input voltage	ICTRL	-1.0	0.01	1.0	μA	VCTRL = 0V or VCTRL = 5V
FLAG output resistance	RFLAG	-	180	450	Ω	IFLAG = 1mA
FLAG output leak current	ILFLAG	ı	0.01	1	μA	VFLAG = 5V
FLAG output delay	TDFLAG	-	2.5	8	ms	
ON resistance	Ron	-	100	140	mΩ	VDD = 5V, IOUT = 500mA
ON resistance	KON	1	140	180	mΩ	VDD = 3.3V, IOUT = 500mA
Short circuit output current	Isc	0.6	-	1.6	Α	VDD = 5V , VOUT = 0V
Output leak current	ILEAK	-	-	10	μA	VCTRL = 0V
Output rise time	Ton1	-	1	4	ms	
Output turn on delay time	Ton2	1	1.3	6	ms	RL = 10Ω , CL = OPEN
Output fall time	Toff1	-	1	20	μs	RL = 1002, CL = OPEN
Output turn off delay time	TOFF2	1	3	20	μs	
Thermal shutdown threshold	TTS	-	135	-	°C	Tj increase
UVLO threshold	VTUVH	2.3	2.5	2.7	V	VDD increasing
O A FO (III E SHOID	VTUVL	2.1	2.3	2.5	V	VDD decreasing

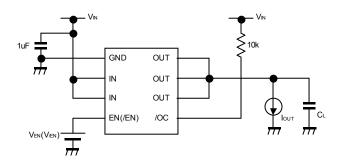
Measurement circuit



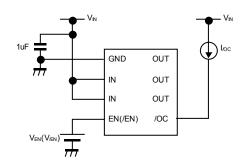
Operating current



EN, /EN input voltage, Output rise, fall time



ON resistance, Over current detection



/OC output LOW voltage

Fig.1 Measurement circuit

●Timing diagram

©BD2041AFJ/BD6519FJ

TOFF1

VOUT

90%

90%

10%

TOFF2

V/EN

50%

Fig.2 Timing diagram

©BD2051AFJ/BD6518FJ

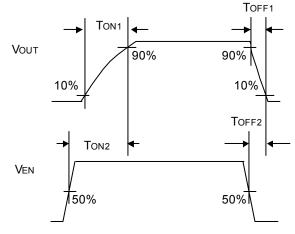
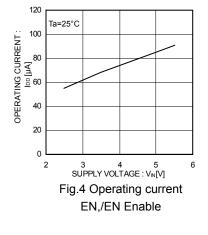
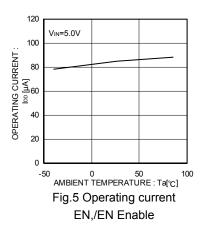


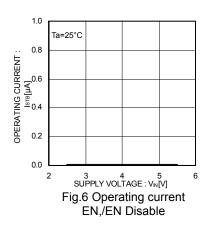
Fig.3 Timing diagram

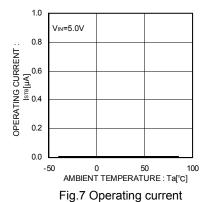
XIN, EN (/EN), and /OC terminal of BD2041AFJ/BD2051AFJ correspond to VDD, CTRL, and FLAG terminal of BD6518FJ/BD6519FJ, respectively.

●Reference data (BD2041AFJ/BD2051AFJ)

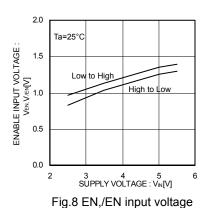


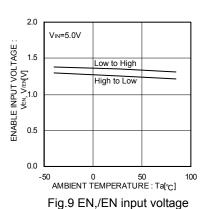


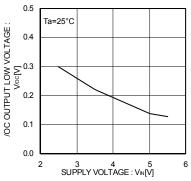


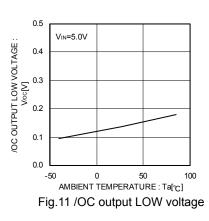


EN,/EN Disable









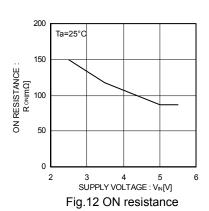
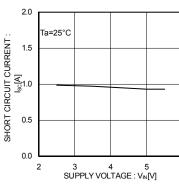


Fig.10 /OC output LOW voltage



2.0 V_{IN=5.0V}

1.5 V_{IN=5.0V}

0.5 O₀ O₀ SO₀ 10 AMBIENT TEMPERATURE : Ta[°C]

VIN=5.0V

150

VIN=5.0V

150

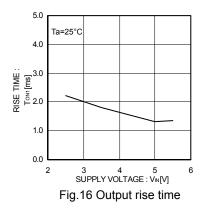
O

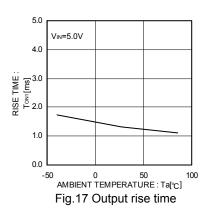
AMBIENT TEMPERATURE: Ta[°C]

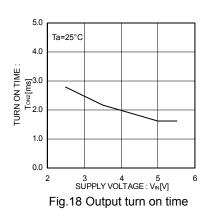
Fig. 13 ON resistance

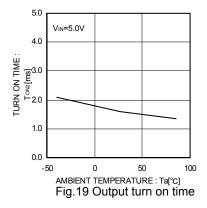
Fig.14 Output current at shortcircuit (BD2041AFJ/51AFJ)

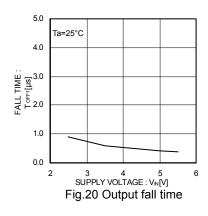
Fig.15 Output current at shortcircuit (BD2041AFJ/51AFJ)

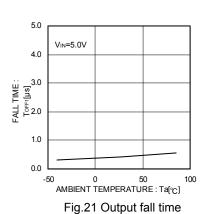


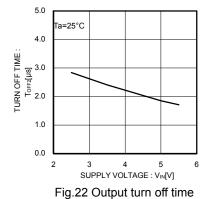


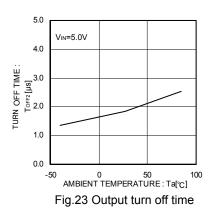


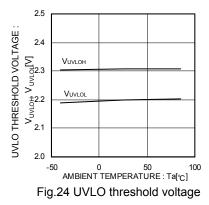












1.0 8.0 UVLO HYSTERESIS VOLTAGE: 0.6 ∑SAH 0.4 0.2 0.0 -50 0 50 100 AMBIENT TEMPERATURE : Ta[°C] Fig.25 UVLO hysteresis voltage

●Waveform data (BD2041AFJ/BD2051AFJ)

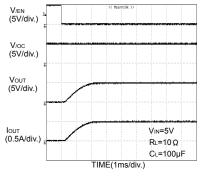


Fig.26 Output rise characteristic (BD2041AFJ)

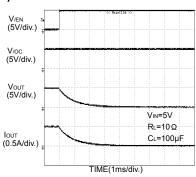


Fig.27 Output fall characteristic (BD2041AFJ)

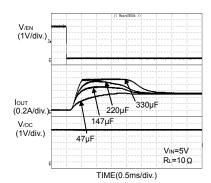


Fig.28 Inush current (BD2041AFJ)

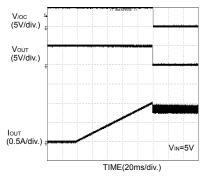


Fig.29 Over current response Ramped load (BD2041AFJ)

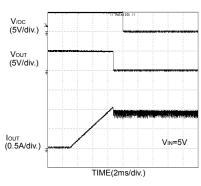


Fig.30 Over current response Ramped load (BD2041AFJ)

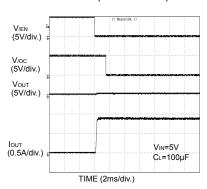


Fig.31 Over current response Enable to shortcircuit (BD2041AFJ)

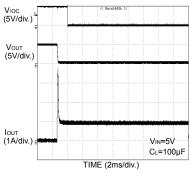


Fig.32 Over current response Output shortcircuit at Enable (BD2041AFJ)

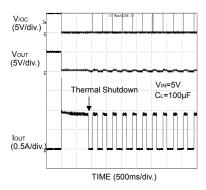


Fig.33 Over current response Output shortcircuit at Enable (BD2041AFJ)

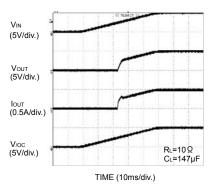


Fig.34 UVLO V_{DD} increasing (BD2041AFJ)

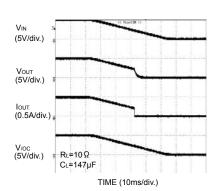
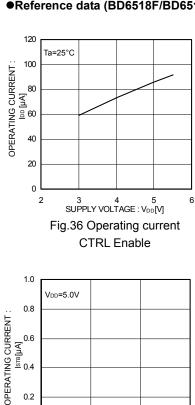


Fig.35 UVLO V_{DD} decreasing (BD2041AFJ)

Regarding the output rise/fall and over current detection characteristics of BD2051AFJ, refer to the characteristic of BD2041AFJ.

●Reference data (BD6518F/BD6519FJ)



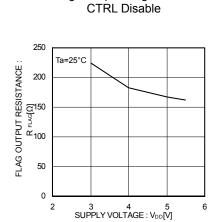


Fig.42 FLAG output resistance

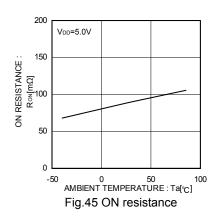
0 50 1
AMBIENT TEMPERATURE : Ta[°C]

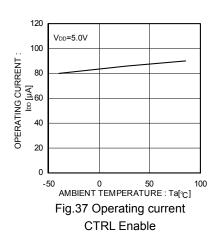
Fig.39 Operating current

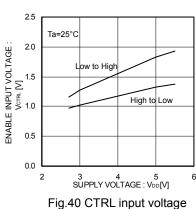
100

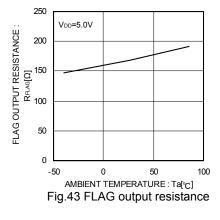
0.0

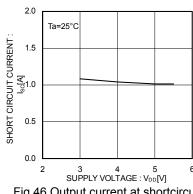
-50

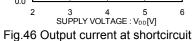


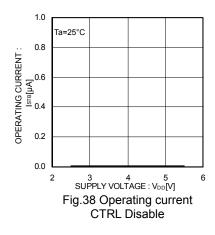


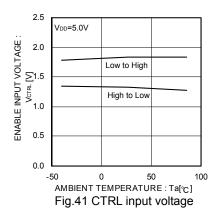


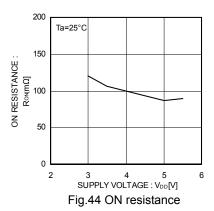












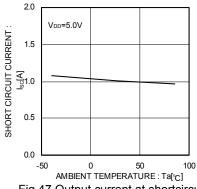


Fig.47 Output current at shortcircuit

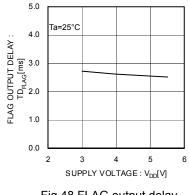


Fig.48 FLAG output delay

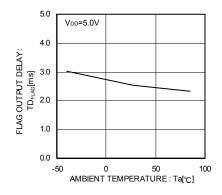


Fig.49 FLAG output delay

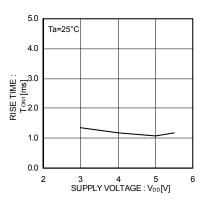


Fig.50 Output rise time

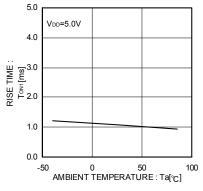


Fig.51 Output rise time

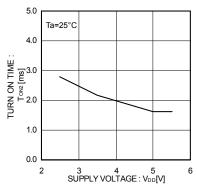


Fig.52 Output turn on delay time

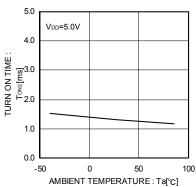


Fig.53 Output turn on delay time

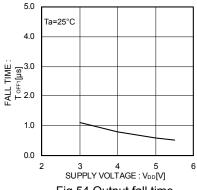
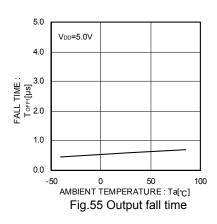


Fig.54 Output fall time



2.7 UVLO THRESHOLD VOLTAGE: 2.6 2.5 2.4 1.4 2.3 2.2 2.1 0 50 AMBIENT TEMPERATURE : Ta[℃]

Fig.58 UVLO threshold voltage

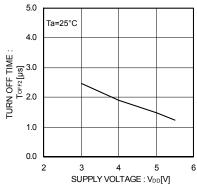


Fig.56 Output turn off delay time

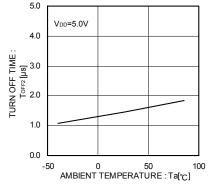


Fig.57 Output turn off delay time

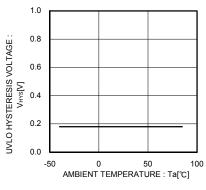
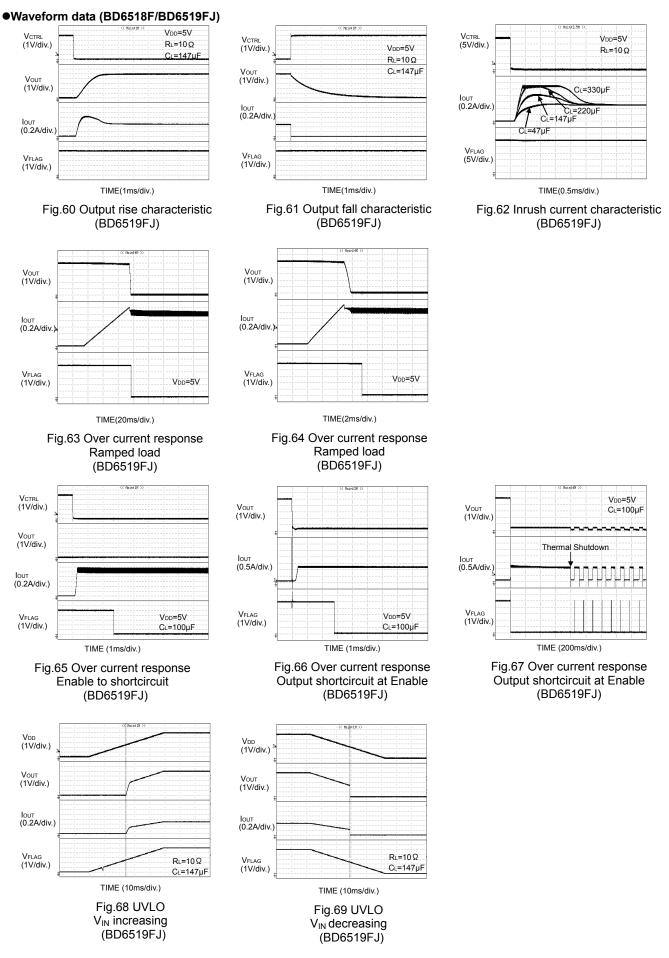


Fig.59 UVLO hysteresis voltage



Regarding the output rise/fall and over current detection characteristics of BD6518FJ, refer to the characteristic of BD6519FJ.

• Block diagram (BD2041AFJ/2051AFJ)

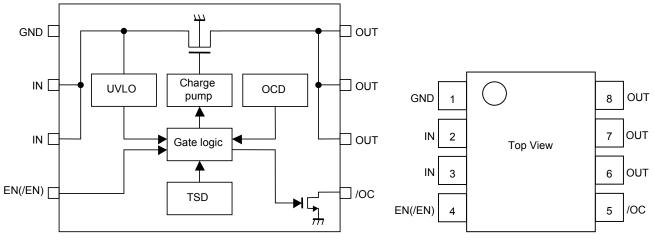


Fig.70 Block diagram

Fig.71 Pin Configuration

●Pin description (BD2041AFJ/2051AFJ)

'in description ((BD2041AFJ/2	(051AFJ)	
Pin No.	Symbol	1/0	Pin function
1	GND	I	Ground.
2, 3	IN	I	Power supply input. Input terminal to the power switch and power supply input terminal of the internal circuit. At use, connect each pin outside.
4	EN (/EN)	I	Enable input. Power switch on at Low level. (BD2041AFJ) Power switch on at High level. (BD2051AFJ) High level input > 2.0V, Low level input < 0.8V.
5	/OC	0	Error flag output. Low at over current, thermal shutdown. Open drain output.
6, 7, 8	OUT	0	Power switch output. At use, connect each pin outside.

●I/O circuit (BD2041AFJ/2051AFJ)

<u> O circuit (BD2041AFJ/2051)</u>	AFJ)	
Symbol	Pin No	Equivalent circuit
EN(/EN)	4	
/OC	5	
OUT	6,7,8	

●Block diagram (BD6518FJ/BD6519FJ)

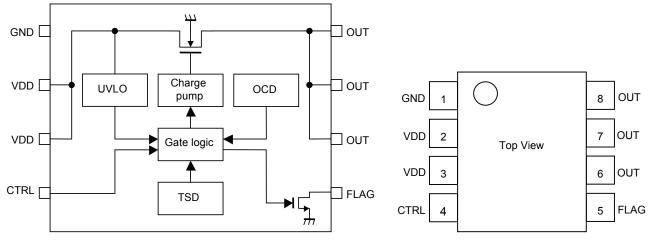


Fig.72 Block diagram

Fig.73 Pin Configuration

●Pin description (BD6518FJ/BD6519FJ)

'in description	(RD6218FJ/RD	76519FJ)	
Pin No.	Symbol	1/0	Pin function
1	GND	1	Ground.
2, 3	VDD	I	Power supply input. Input terminal to the power switch and power supply input terminal of the internal circuit. At use, connect each pin outside.
4	CTRL	I	Enable input. Power switch on at High level. (BD6518FJ) Power switch on at Low level. (BD6519FJ) High level input > 2.5V, Low level input < 0.7V.
5	FLAG	0	Error flag output. Low at over current, thermal shutdown. Open drain output.
6, 7, 8	OUT	0	Power switch output. At use, connect each pin outside.

●I/O circuit (BD6518F.I/BD6519F.I)

<u>/O circuit (BD6518FJ/BD65</u>	19FJ)	
Symbol	Pin No	Equivalent circuit
CTRL	4	
FLAG	5	
OUT	6,7,8	

●Functional description (BD2041AFJ/2051AFJ)

1. Switch operation

IN terminal and OUT terminal are connected to the drain and the source of switch MOSFET respectively. And the IN terminal is used also as power source input to internal control circuit.

When the switch is turned on from EN/EN control input, IN terminal and OUT terminal are connected by a $80m\Omega$ switch. In on status, the switch is bidirectional. Therefore, when the potential of OUT terminal is higher than that of IN terminal, current flows from OUT terminal to IN terminal.

Since a parasitic diode between the drain and the source of switch MOSFET is canceled, in the off status, it is possible to prevent current from flowing reversely from OUT to IN.

2. Thermal shutdown circuit (TSD)

If over current would continue, the temperature of the IC would increase drastically. If the junction temperature were beyond 140°C (typ.) in the condition of over current detection, thermal shutdown circuit operates and makes power switch turn off and outputs error flag (/OC). Then, when the junction temperature decreases lower than 120°C (typ.), power switch is turned on and error flag (/OC) is cancelled. Unless the fact of the increasing chips temperature is removed or the output of power switch is turned off, this operation repeats.

The thermal shutdown circuit operates when the switch is on (EN,/EN signal is active).

3. Over current detection (OCD)

The over current detection circuit limits current (I_{SC}) and outputs error flag (/OC) when current flowing in each switch MOSFET exceeds a specified value. There are three types of response against over current. The over current detection circuit works when the switch is on (EN,/EN signal is active).

3-1. When the switch is turned on while the output is in shortcircuit status

When the switch is turned on while the output is in shortcircuit status or so, the switch gets in current limit status soon.

3-2. When the output shortcircuits while the switch is on

When the output shortcircuits or large capacity is connected while the switch is on, very large current flows until the over current limit circuit reacts. When the current detection, limit circuit works, current limitation is carried out.

3-3. When the output current increases gradually

When the output current increases gradually, current limitation does not work until the output current exceeds the over current detection value. When it exceeds the detection value, current limitation is carried out.

4. Under voltage lockout (UVLO)

UVLO circuit prevents the switch from turning on until the VIN exceeds 2.3V(Typ.). If the VIN drops below 2.2V(Typ.) while the switch turns on, then UVLO shuts off the power switch. UVLO has hysteresis of a 100mV(Typ). Under voltage lockout circuit works when the switch is on (EN,/EN signal is active).

5. Error flag (/OC) output

Error flag output is N-MOS open drain output. At detection of over current, thermal shutdown, low level is output.

Over current detection has delay filter. This delay filter prevents instantaneous current detection such as inrush current at switch on, hot plug from being informed to outside.

●Functional description (BD6518FJ/BD6519FJ)

1. Switch operation

VDD terminal and OUT terminal are connected to the drain and the source of switch MOSFET respectively. And the VDD terminal is used also as power source input to internal control circuit.

When the switch is turned on from CTRL control input, VDD terminal and OUT terminal are connected by a $100m\Omega$ switch. In on status, the switch is bidirectional. Therefore, when the potential of OUT terminal is higher than that of VDD terminal, current flows from OUT terminal to VDD terminal.

Since a parasitic diode between the drain and the source of switch MOSFET is canceled, in the off status, it is possible to prevent current from flowing reversely from OUT to VDD.

2. Thermal shutdown circuit (TSD)

If over current would continue, the temperature of the IC would increase drastically. If the junction temperature were beyond 135°C (typ.) in the condition of over current detection, thermal shutdown circuit operates and makes power switch turn off and outputs error flag (FALG). Then, when the junction temperature decreases lower than 125°C (typ.), power switch is turned on and error flag (FLAG) is cancelled. Unless the fact of the increasing chips temperature is removed or the output of power switch is turned off, this operation repeats.

The thermal shutdown circuit operates when the switch is on (CTRL signal is active).

3. Over current detection (OCD)

The over current detection circuit limits current (I_{SC}) and outputs error flag (FLAG) when current flowing in each switch MOSFET exceeds a specified value. There are three types of response against over current. The over current detection circuit works when the switch is on (CTRL signal is active).

- 3-1. When the switch is turned on while the output is in shortcircuit status

 When the switch is turned on while the output is in shortcircuit status or so, the switch gets in current limit status soon.
- 3-2. When the output shortcircuits while the switch is on When the output shortcircuits or large capacity is connected while the switch is on, very large current flows until the over current limit circuit reacts. When the current detection, limit circuit works, current limitation is carried out.

3-3. When the output current increases gradually

When the output current increases gradually, current limitation does not work until the output current exceeds the over current detection value. When it exceeds the detection value, current limitation is carried out.

4. Under voltage lockout (UVLO)

UVLO circuit prevents the switch from turning on until the VDD exceeds 2.5V(Typ.). If the VDD drops below 2.3V(Typ.) while the switch turns on, then UVLO shuts off the power switch. UVLO has hysteresis of a 200mV(Typ). Under voltage lockout circuit works when the switch is on (CTRL signal is active).

5. Error flag (FLAG) output

Error flag output (FLAG) is N-MOS open drain output. At detection of over current, thermal shutdown, low level is output.

Over current detection has delay filter on 2.5ms(Typ.). This delay filter prevents instantaneous current detection such as inrush current at switch on, hot plug from being informed to outside.

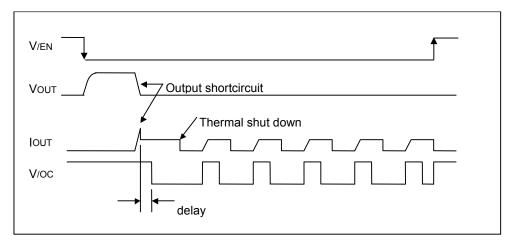


Fig.74 Over current detection, thermal shutdown timing (BD2041AFJ/BD6519FJ)

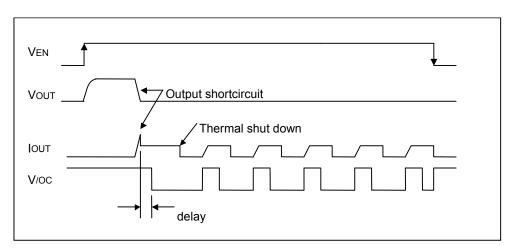


Fig.75 Over current detection, thermal shutdown timing (BD2051AFJ/BD6518FJ)

WIN, EN (/EN), and /OC terminal of BD2041AFJ/BD2051AFJ correspond to VDD, CTRL, and FLAG terminal of BD6518FJ/BD6519FJ, respectively.

●Typical application circuit

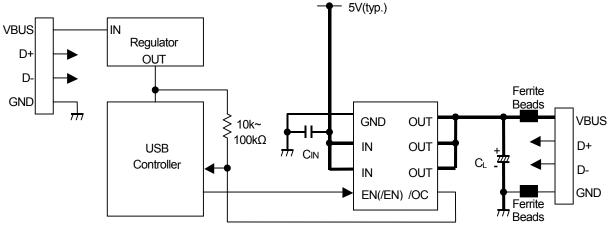


Fig.76 Typical application circuit (BD2041AFJ/51AFJ)

Application information

When excessive current flows owing to output shortcircuit or so, ringing occurs by inductance of power source line to IC, and may cause bad influences upon IC actions. In order to avoid this case, connect a bypath capacitor by IN terminal and GND terminal of IC. 1µF or higher is recommended.

Pull up /OC output by resistance $10k\Omega \sim 100k\Omega$.

Set up value which satisfies the application as CL and Ferrite Beads.

This system connection diagram doesn't guarantee operating as the application.

The external circuit constant and so on is changed and it uses, in which there are adequate margins by taking into account external parts or dispersion of IC including not only static characteristics but also transient characteristics.

W IN, EN (/EN), and /OC terminal of BD2041AFJ/BD2051AFJ correspond to VDD, CTRL, and FLAG terminal of BD6518FJ/BD6519FJ, respectively.

Power dissipation character

(SOP-J8)

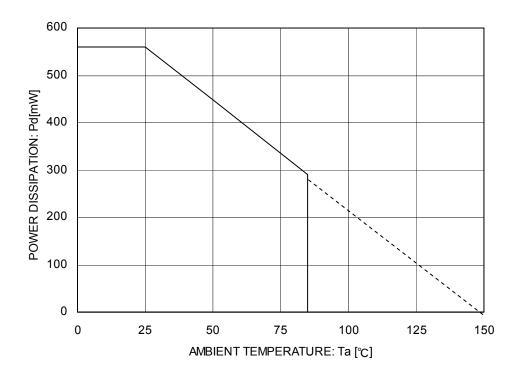


Fig.77 Power dissipation curve (Pd-Ta Curve)

Notes for use

(1) Absolute Maximum Ratings

An excess in the absolute maximum ratings, such as supply voltage, temperature range of operating conditions, etc., can break down devices, thus making impossible to identify breaking mode such as a short circuit or an open circuit. If any special mode exceeding the absolute maximum ratings is assumed, consideration should be given to take physical safety measures including the use of fuses, etc.

(2) Operating conditions

These conditions represent a range within which characteristics can be provided approximately as expected. The electrical characteristics are guaranteed under the conditions of each parameter.

(3) Reverse connection of power supply connector

The reverse connection of power supply connector can break down ICs. Take protective measures against the breakdown due to the reverse connection, such as mounting an external diode between the power supply and the IC's power supply terminal.

(4) Power supply line

Design PCB pattern to provide low impedance for the wiring between the power supply and the GND lines. In this regard, for the digital block power supply and the analog block power supply, even though these power supplies has the same level of potential, separate the power supply pattern for the digital block from that for the analog block, thus suppressing the diffraction of digital noises to the analog block power supply resulting from impedance common to the wiring patterns. For the GND line, give consideration to design the patterns in a similar manner.

Furthermore, for all power supply terminals to ICs, mount a capacitor between the power supply and the GND terminal. At the same time, in order to use an electrolytic capacitor, thoroughly check to be sure the characteristics of the capacitor to be used present no problem including the occurrence of capacity dropout at a low temperature, thus determining the constant.

(5) GND voltage

Make setting of the potential of the GND terminal so that it will be maintained at the minimum in any operating state. Furthermore, check to be sure no terminals are at a potential lower than the GND voltage including an actual electric transient

(6) Short circuit between terminals and erroneous mounting

In order to mount ICs on a set PCB, pay thorough attention to the direction and offset of the ICs. Erroneous mounting can break down the ICs. Furthermore, if a short circuit occurs due to foreign matters entering between terminals or between the terminal and the power supply or the GND terminal, the ICs can break down.

(7) Operation in strong electromagnetic field

Be noted that using ICs in the strong electromagnetic field can malfunction them.

(8) Inspection with set PCB

On the inspection with the set PCB, if a capacitor is connected to a low-impedance IC terminal, the IC can suffer stress. Therefore, be sure to discharge from the set PCB by each process. Furthermore, in order to mount or dismount the set PCB to/from the jig for the inspection process, be sure to turn OFF the power supply and then mount the set PCB to the jig. After the completion of the inspection, be sure to turn OFF the power supply and then dismount it from the jig. In addition, for protection against static electricity, establish a ground for the assembly process and pay thorough attention to the transportation and the storage of the set PCB.

(9) Input terminals

In terms of the construction of IC, parasitic elements are inevitably formed in relation to potential. The operation of the parasitic element can cause interference with circuit operation, thus resulting in a malfunction and then breakdown of the input terminal. Therefore, pay thorough attention not to handle the input terminals, such as to apply to the input terminals a voltage lower than the GND respectively, so that any parasitic element will operate. Furthermore, do not apply a voltage to the input terminals when no power supply voltage is applied to the IC. In addition, even if the power supply voltage is applied, apply to the input terminals a voltage lower than the power supply voltage or within the guaranteed value of electrical characteristics.

(10) Ground wiring pattern

If small-signal GND and large-current GND are provided, It will be recommended to separate the large-current GND pattern from the small-signal GND pattern and establish a single ground at the reference point of the set PCB so that resistance to the wiring pattern and voltage fluctuations due to a large current will cause no fluctuations in voltages of the small-signal GND. Pay attention not to cause fluctuations in the GND wiring pattern of external parts as well.

(11) External capacitor

In order to use a ceramic capacitor as the external capacitor, determine the constant with consideration given to a degradation in the nominal capacitance due to DC bias and changes in the capacitance due to temperature, etc.

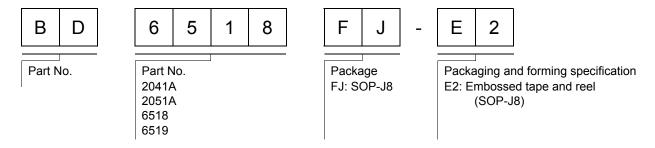
(12) Thermal shutdown circuit (TSD)

When junction temperatures become detected temperatures or higher, the thermal shutdown circuit operates and turns a switch OFF. The thermal shutdown circuit, which is aimed at isolating the LSI from thermal runaway as much as possible, is not aimed at the protection or guarantee of the LSI. Therefore, do not continuously use the LSI with this circuit operating or use the LSI assuming its operation.

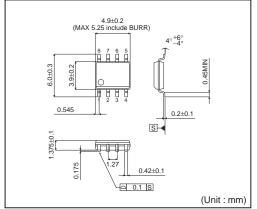
(13) Thermal design

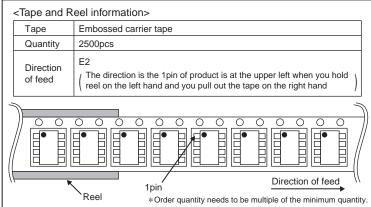
Perform thermal design in which there are adequate margins by taking into account the power dissipation (Pd) in actual states of use.

Ordering part number



SOP-J8





Notes

No copying or reproduction of this document, in part or in whole, is permitted without the consent of ROHM Co.,Ltd.

The content specified herein is subject to change for improvement without notice.

The content specified herein is for the purpose of introducing ROHM's products (hereinafter "Products"). If you wish to use any such Product, please be sure to refer to the specifications, which can be obtained from ROHM upon request.

Examples of application circuits, circuit constants and any other information contained herein illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

Great care was taken in ensuring the accuracy of the information specified in this document. However, should you incur any damage arising from any inaccuracy or misprint of such information, ROHM shall bear no responsibility for such damage.

The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM and other parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the use of such technical information.

The Products specified in this document are intended to be used with general-use electronic equipment or devices (such as audio visual equipment, office-automation equipment, communication devices, electronic appliances and amusement devices).

The Products specified in this document are not designed to be radiation tolerant.

While ROHM always makes efforts to enhance the quality and reliability of its Products, a Product may fail or malfunction for a variety of reasons.

Please be sure to implement in your equipment using the Products safety measures to guard against the possibility of physical injury, fire or any other damage caused in the event of the failure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM shall bear no responsibility whatsoever for your use of any Product outside of the prescribed scope or not in accordance with the instruction manual.

The Products are not designed or manufactured to be used with any equipment, device or system which requires an extremely high level of reliability the failure or malfunction of which may result in a direct threat to human life or create a risk of human injury (such as a medical instrument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel-controller or other safety device). ROHM shall bear no responsibility in any way for use of any of the Products for the above special purposes. If a Product is intended to be used for any such special purpose, please contact a ROHM sales representative before purchasing.

If you intend to export or ship overseas any Product or technology specified herein that may be controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to obtain a license or permit under the Law.



Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/